

## Topic 6

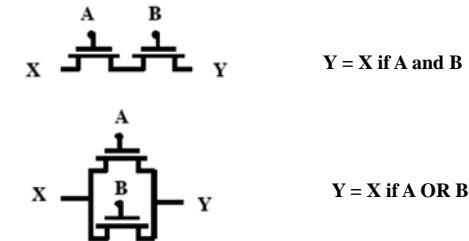
### CMOS Static & Dynamic Logic Gates

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## NMOS Transistors in Series/Parallel Connection

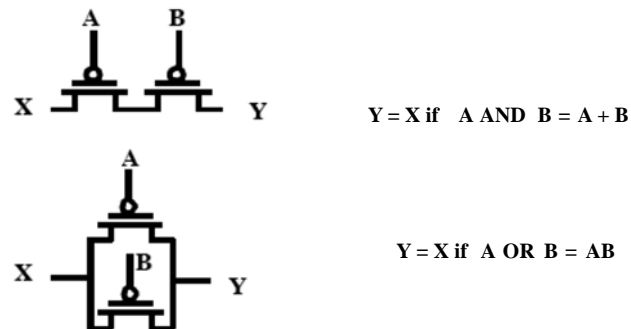
- ◆ Transistors can be thought as a switch controlled by its gate signal
- ◆ NMOS switch closes when switch control input is high



NMOS Transistors pass a “strong” 0 but a “weak” 1

## PMOS Transistors in Series/Parallel Connection

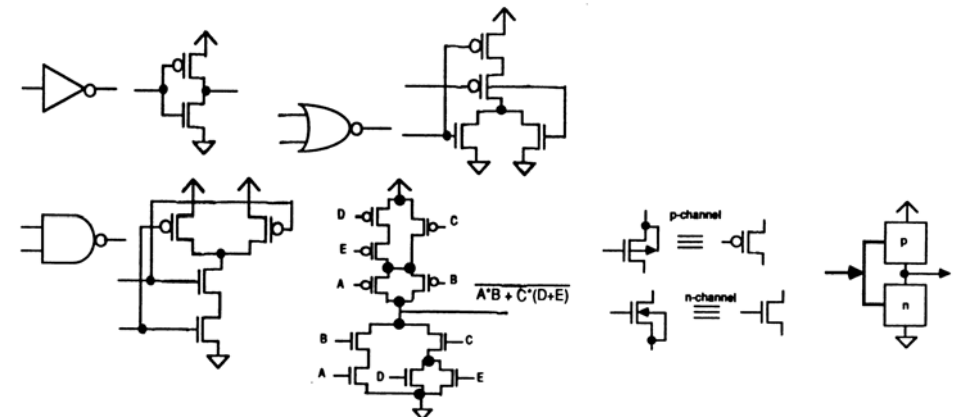
PMOS switch closes when switch control input is low



PMOS Transistors pass a “strong” 1 but a “weak” 0

## Static CMOS Circuit

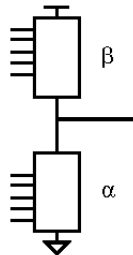
- ◆ Basic CMOS combinational circuits consist of:
  - Complementary pull-up (p-type) and pull-down (n-type)



## Static CMOS

To build a logic gate  $\bar{f}(x_1, \dots, x_n)$ , need to build two switch networks:

The pullup network connects the output to  $V_{DD}$  when  $f$  is false.



The pulldown network connects the output to  $GND$  when  $f$  is true.

Pulldown

$$\alpha(x_1, \dots, x_n) = f(x_1, \dots, x_n)$$

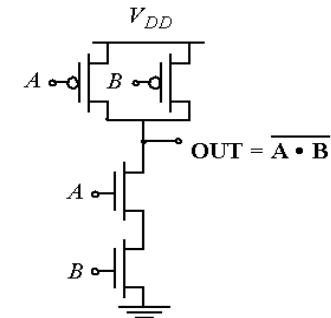
Pullup

$$\beta(\bar{x}_1, \dots, \bar{x}_n) = \bar{f}(x_1, \dots, x_n) \quad (\text{since pMOS invert inputs})$$

## Example Gate: NAND

A	B	Out
0	0	1
0	1	1
1	0	1
1	1	0

Truth Table of a 2 input NAND gate



PDN:  $G = A \cdot B \Rightarrow$  Conduction to  $GND$

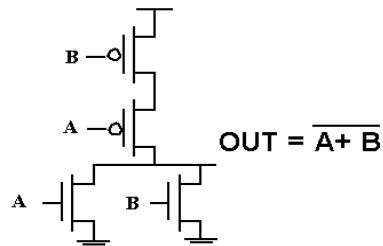
PUN:  $F = \bar{A} + \bar{B} = \overline{A \cdot B} \Rightarrow$  Conduction to  $V_{DD}$

$$\overline{G(In_1, In_2, In_3, \dots)} \equiv F(\bar{In}_1, \bar{In}_2, \bar{In}_3, \dots)$$

## Example Gate: NOR

A	B	Out
0	0	1
0	1	0
1	0	0
1	1	0

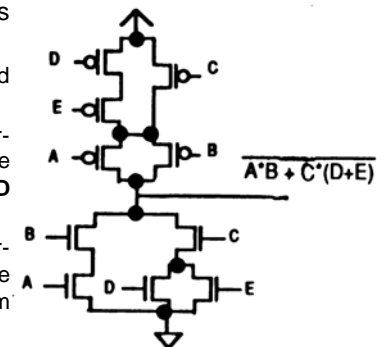
Truth Table of a 2 input NOR gate



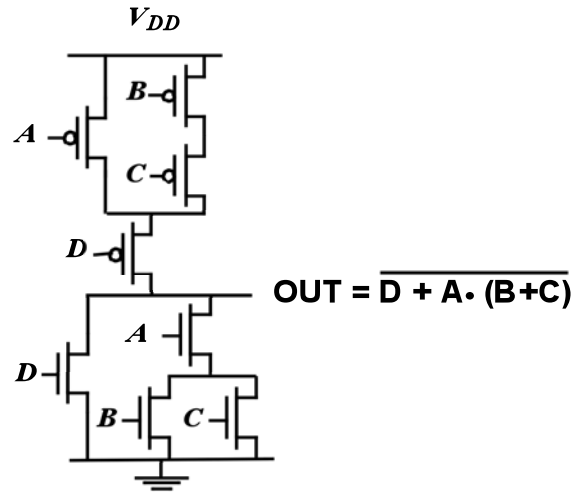
## Complex Gate

◆ We can form complex combinational circuit function in a complementary tree. The procedure to construct a complementary tree is as follow:-

- Express the boolean expression in an inverted form
- For the n-transistor tree, working from the inner-most bracket to the outer-most term, connect the **OR** term transistors in parallel, and the **AND** term transistors in series
- For the p-transistor tree, working from the inner-most bracket to the outer-most term, connect the **OR** term transistors in series, and the **AND** term transistors in parallel



## Example Gate: COMPLEX CMOS GATE



## Properties of Complementary CMOS Gates

### 1) High noise margins

$V_{OH}$  and  $V_{OL}$  are at  $V_{DD}$  and  $GND$ , respectively.

### 2) No static power consumption

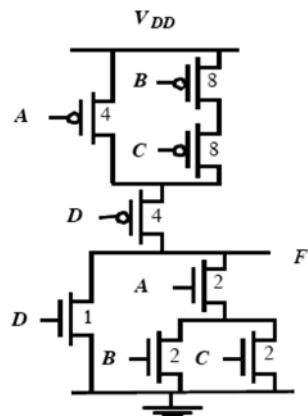
There never exists a direct path between  $V_{DD}$  and  $V_{SS}$  ( $GND$ ) in steady-state mode

### 3) Comparable rise and fall times:

(under the appropriate scaling conditions)

## Transistor Sizing

- for symmetrical response (dc, ac)
- for performance

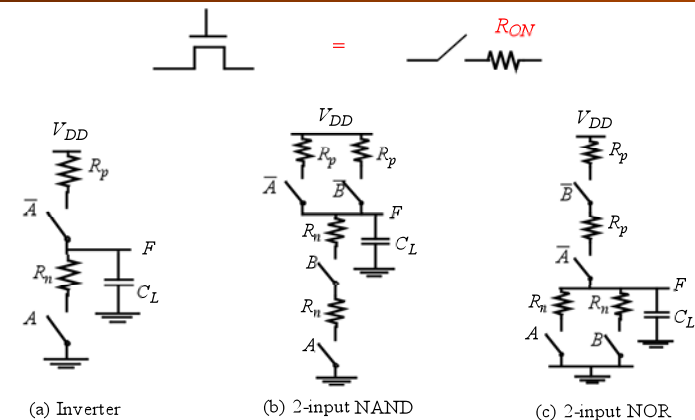


Input Dependent

Focus on worst-case

- assume  $\mu_n = 2 \cdot \mu_p$  (i.e. n-channel transistors has 2 times the transconductance as that of p-channel.)

## Propagation Delay Analysis - The Switch Model



$$t_p = 0.69 R_{on} C_L$$

(assuming that  $C_L$  dominates!)

## What is the Value of $R_{on}$ ?

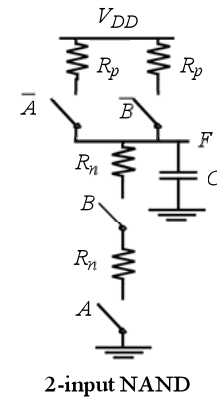
- Depends strongly on the operating region
- For hand analysis use a fixed value of  $R$  which is the average of the two end points of the transition
- Similar to the previous approach of averaging currents

**EXAMPLE:** For  $t_{pHL}$  for an inverter, the  $R_{on}$  is:

$$R_{on} = \frac{1}{2}(R_{NMOS}(V_{out} = V_{DD}) + R_{NMOS}(V_{out} = V_{DD}/2))$$

$$= \frac{1}{2} \left( \left( \frac{V_{DS}}{I_D} \right)_{V_{out} = V_{DD}} + \left( \frac{V_{DS}}{I_D} \right)_{V_{out} = V_{DD}/2} \right)$$

## Analysis of Propagation Delay



2-input NAND

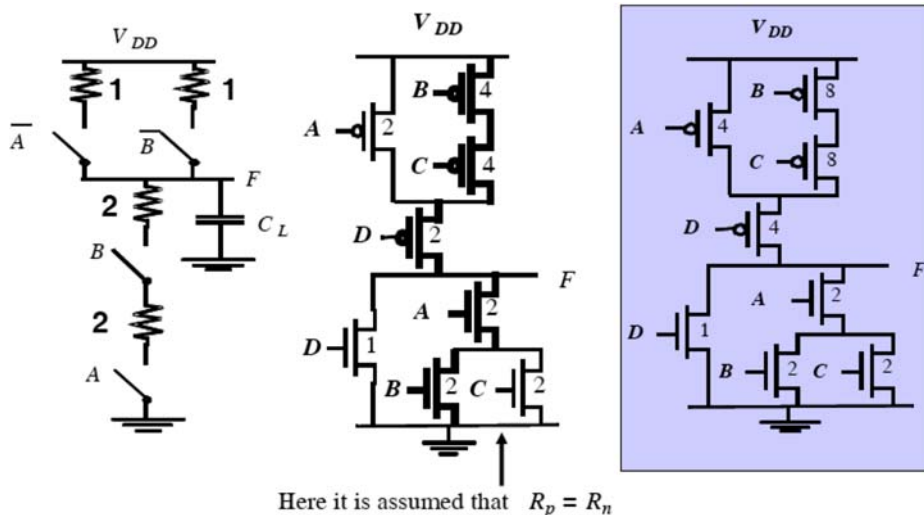
1. Assume  $R_n = R_p$  = resistance of minimum sized NMOS inverter
2. Determine "Worst Case Input" transition (Delay depends on input values)
3. Example:  $t_{pLH}$  for 2input NAND
  - Worst case when only ONE PMOS Pulls up the output node
  - For 2 PMOS devices in parallel, the resistance is lower

$$t_{pLH} = 0.69 R_p C_L$$

4. Example:  $t_{pHL}$  for 2input NAND
  - Worst case : TWO NMOS in series

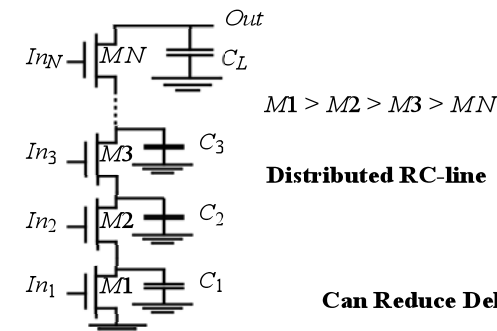
$$t_{pHL} = 0.69 (2R_n) C_L$$

## Design for Worst Case



## Fast Complex Gate - Design Techniques

- Transistor Sizing:  
As long as Fan-out Capacitance dominates
- Progressive Sizing:



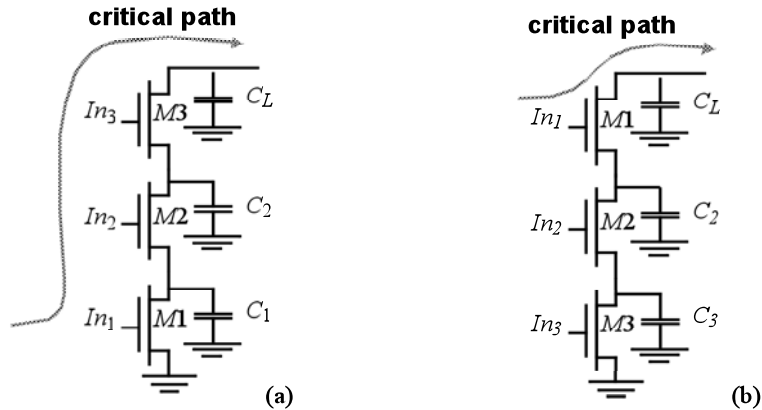
$$M1 > M2 > M3 > MN$$

**Distributed RC-line**

**Can Reduce Delay with more than 30%!**

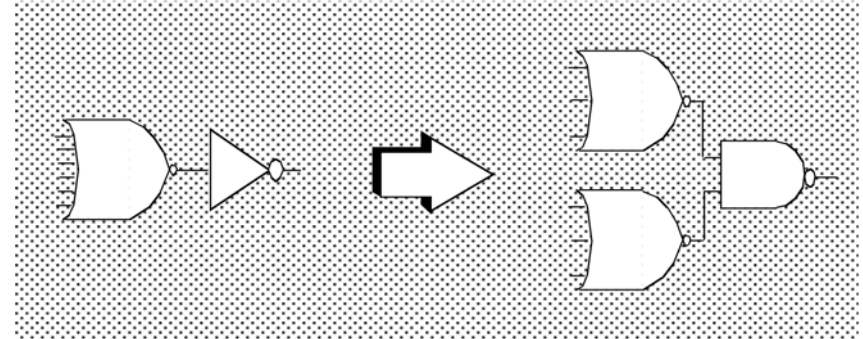
## Fast Complex Gate - Design Techniques (2)

- Transistor Ordering



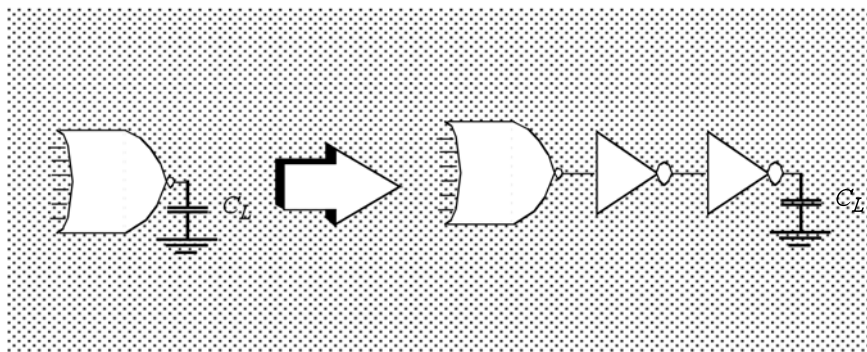
## Fast Complex Gate - Design Techniques (3)

- Improved Logic Design

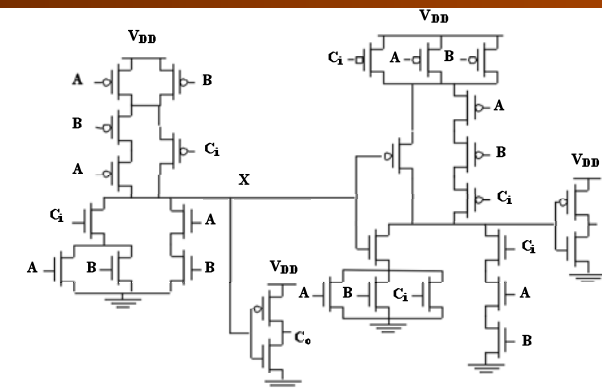


## Fast Complex Gate - Design Techniques (4)

- Buffering: Isolate Fan-in from Fan-out



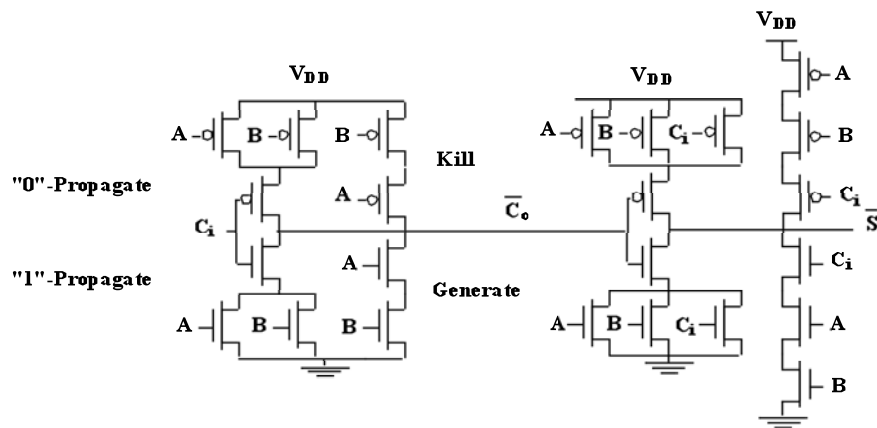
## Example: Full Adder



$$C_o = AB + C_i(A+B)$$

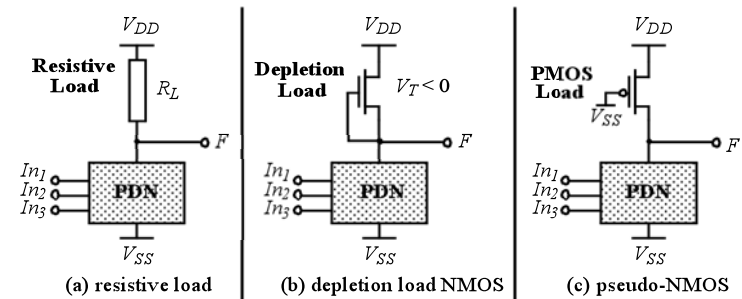
28 transistors

## A Revised Adder Circuit



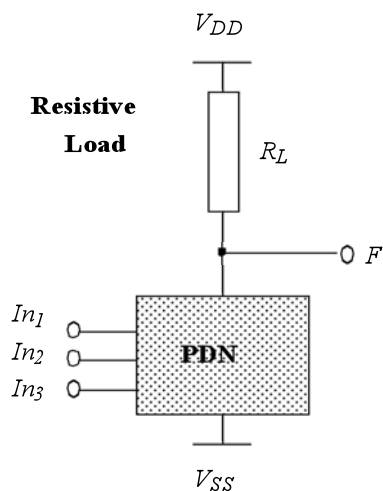
24 transistors

## Ratioed Logic



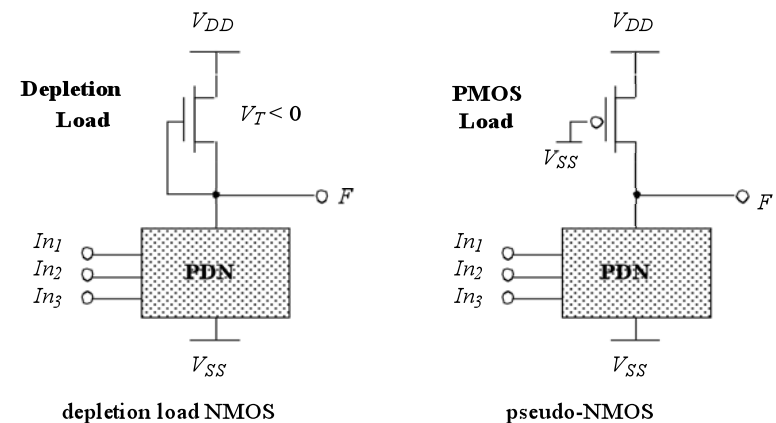
Goal: to reduce the number of devices over complementary CMOS

## Ratioed Logic



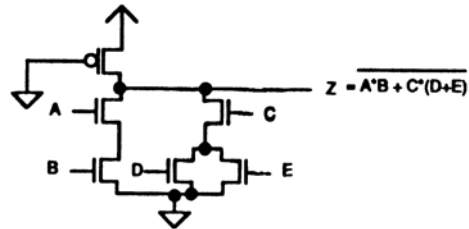
- N transistors + Load
- $V_{OH} = V_{DD}$
- $V_{OL} = \frac{R_{PN}}{R_{PN} + R_L}$
- Asymmetrical response
- Static power consumption
- $t_{pL} = 0.69 R_L C_L$

## Active Loads



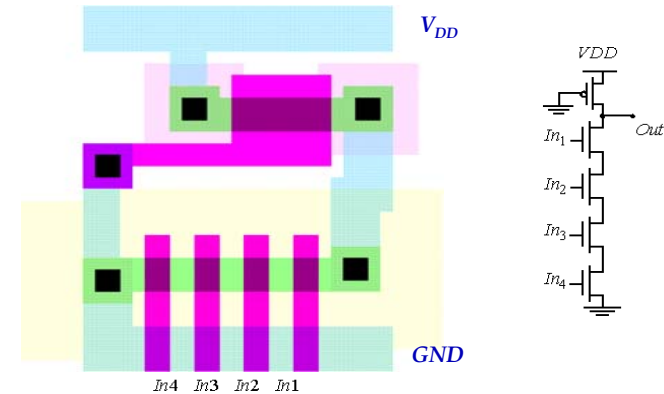
## Psuedo NMOS

- ◆ *Disadvantages of previous circuit :*
  - Almost twice as many transistors as equivalent NMOS implementation.
  - If there are too many series transistors in the tree, switching speed is reduced.
- ◆ Try a pseudo NMOS circuit:-



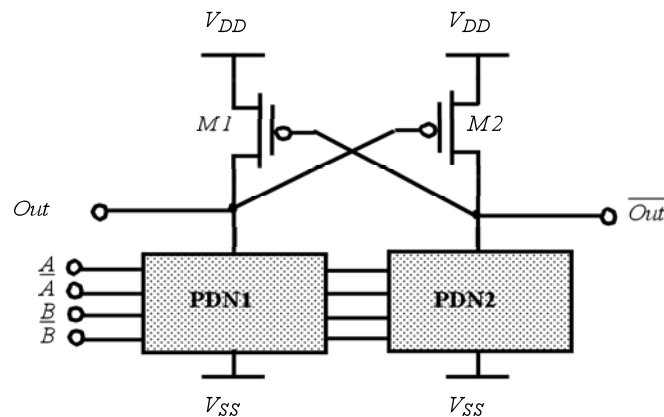
- ◆ The pull-up p-channel transistor is always conducting.
  - *Disadvantages:* high d.c. dissipation & slow rise time.

## Pseudo-NMOS NAND Gate



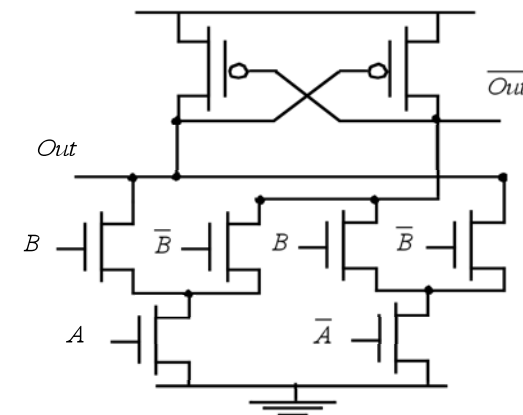
$$C_{L,pseudo} = 0.5 C_{L,CMOS} \text{ (Fan-out of 1)}$$

## Improved Loads (1)



## Dual Cascode Voltage Switch Logic (DCVSL)

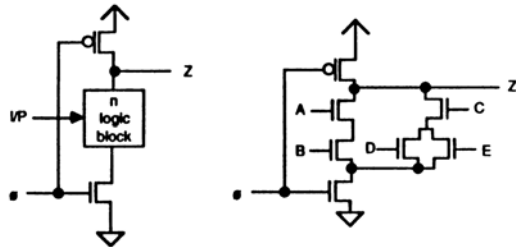
## Example



## XOR-NXOR gate

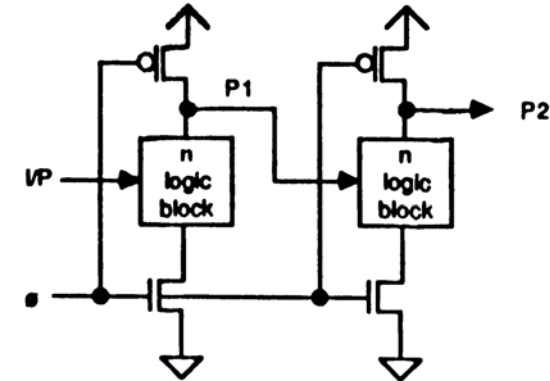
## Dynamic Logic

- There is another class of logic gates which relies on the use of a clock signal. This class of circuit is known as *dynamic circuits*. The clock signal is used to divide the gate operation into two halves. In the first half, the output node is **pre-charged** to a high or low logic state. In the second half of a clock cycle, the circuit **evaluates** the correct output state.
- When  $\phi$  is low, Z is charged to high. When  $\phi$  is high, n logic block evaluates input, and conditionally discharges Z. This circuit adds series resistance to the pull-down n-channel transistor, therefore the fall time is increased slightly.
- This circuit is *dynamic* because during evaluation, the output high level at Z is maintained by the stray capacitance at the output node. If  $\phi$  stays high (i.e. evaluation period) for a long time, Z may eventually discharge to a low logic level.



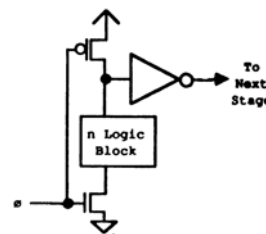
## Problem with Cascading Dynamic Logic

- Problem with cascading such as a circuit:-
  - Inputs can only be changed when  $\phi$  is low and must be stable when  $\phi$  is high.
  - When  $\phi$  is low, both P1 and P2 are precharged to a high voltage. However when  $\phi$  is high, delay through on the output P1 may erroneously discharge P2.

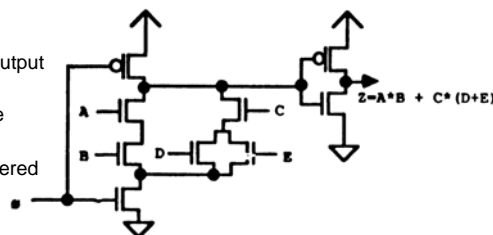


## CMOS Domino Logic

- Solution to the above problem:-
  - Add an inverter to ensure that the output is low during precharge, and prevent the next stage from evaluating, until the current stage has finished evaluation.
  - This ensures that each stage (at the output of the inverter) will make at most a single transition from 0 -> 1.
  - When many stages are cascaded, evaluation proceeds from one stage to the next - similar to dominoes falling one after another.

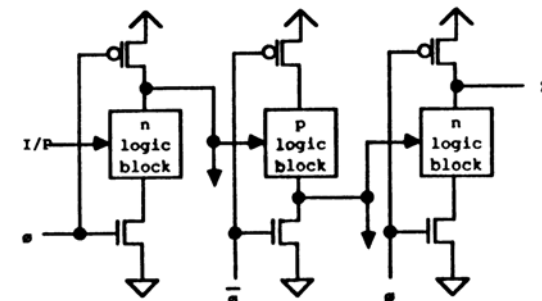


- Disadvantages of domino logic:-
  - Only non-inverting logic is possible, i.e. output also high active
  - Each gate needs an inverter; hence more transistors
  - Suffer from charge sharing effect (considered later)



## Alternating dynamic logic (1)

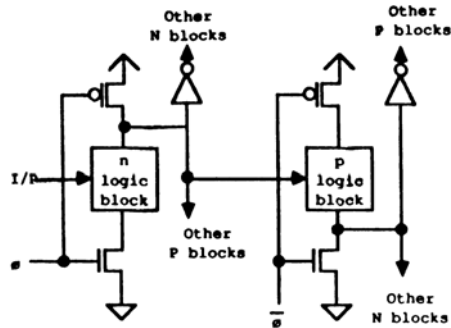
- Another possible scheme is to use alternate n and p logic blocks as shown below.
- In this scheme, each alternate stage is pre-charged high and low. Each stage uses alternate n and p transistors to implement the gate function. Stage 1 makes at most one high to low transition, while stage 2 makes at most one low to high transition for each evaluation. Since the p logic block will only change state if input is a low, this circuit behaves like the domino logic.





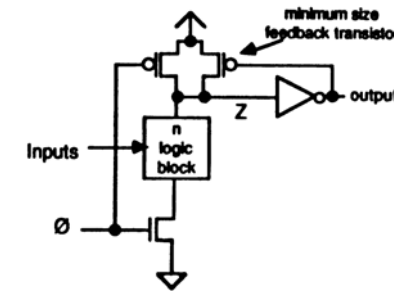
## Alternating dynamic logic (2)

- A slight variation of this circuit is shown below, where an inverter is added per stage to increase flexibility. Here each stage can drive either n or p blocks and both low active and high active logic can be implemented.



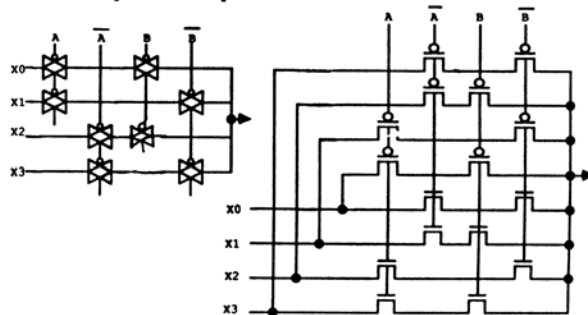
## Making a Dynamic Gate static

- Finally, by adding a feedback pullup, we can make the circuit static.
- This circuit turns the originally **dynamic** gate into a **static** gate because the feedback transistor can maintain a logic high level at the node Z for an indefinite length of time. Without this feedback transistor, the charge stored at the node Z will eventually leak away.



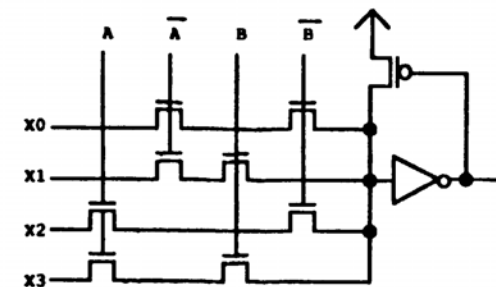
## Pass Transistor Logic

- An alternative design style is to use pass transistors. The following is an example of a multiplexer.
- Complementary transmission gates are used here because n-channel pass transistors will pass 0 logic level well but, 1 logic level poorly. This is because in order for the n-transistor to be **ON**,  $V_{gs}$  must be greater than  $V_{th}$ . Therefore each series n transistor will degrade the 1 logic level by  $V_{th}$ . The opposite is true with p-channel pass transistors: 0 logic level is passed poorly.



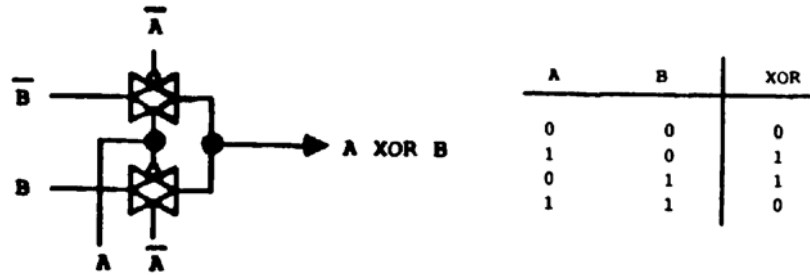
## Pass Transistor Logic with feedback

- This circuit uses only n transistors, therefore it is economical on transistor count. In order to ensure that the 1 logic level is passed properly, a p pull-up transistor is added. This restores the 1 logic level at the input of the inverter.

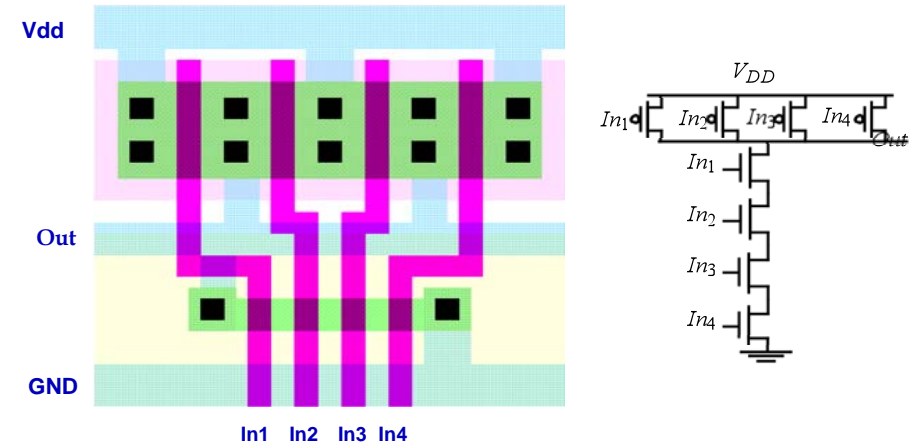


## Pass Transistor XOR gate

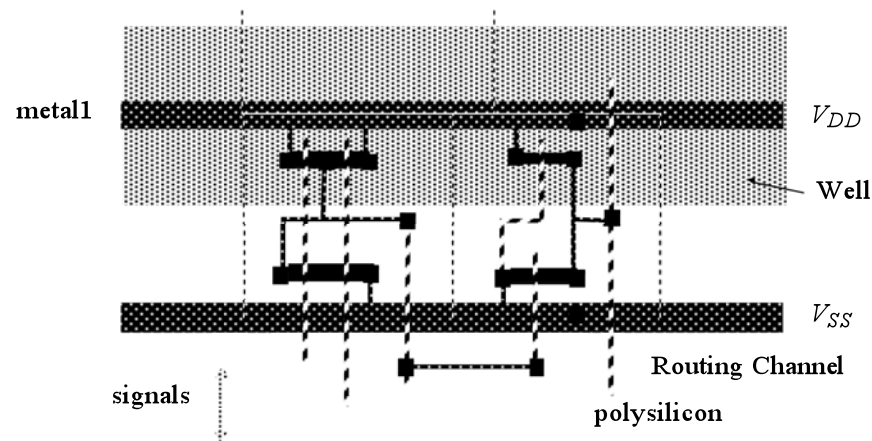
- Pass transistor logic can sometimes be very economical in implementing logic functions. For example, an **XOR** gate can be implemented with just two transmission gates:-



## 4-input NAND Gate



## Standard Cell Layout Methodology



## Two Versions of (a+b).c

